

SEL955-02

Infrared Emitting Diodes(GaAs)

The SEL955-02 is GaAs infrared emitting diode that is designed for high power, low forward voltage and high speed rise / fall time.

This device is optimized for speed and efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current.

Features

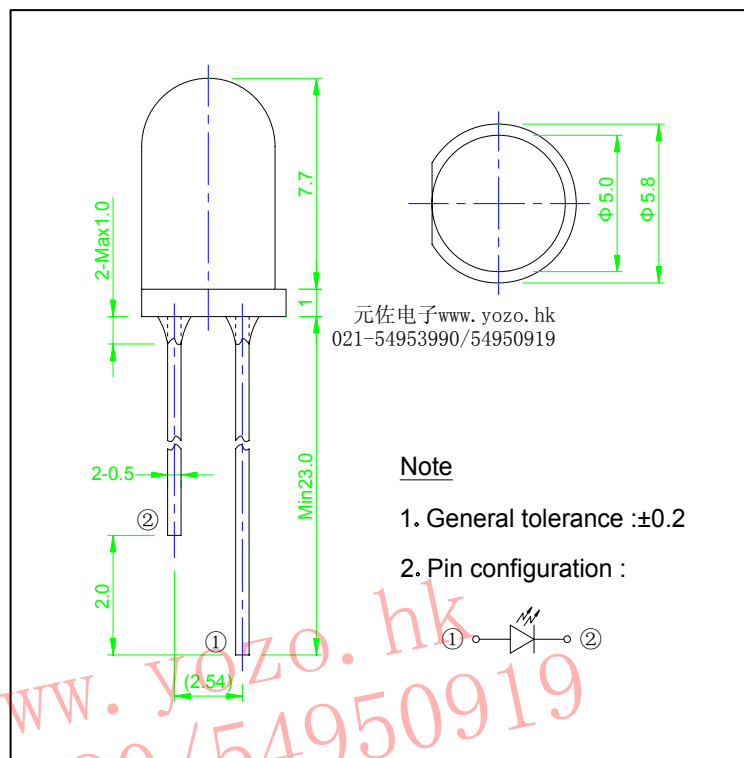
- 940nm wavelength
- Low forward voltage
- High power and high reliability
- Available for pulse operating

Application

- IR Audio and Telephone
- Communication
- Optical Switch
- Smoke Sensor
- Touch Screen

DIMENSIONS

(Unit:mm)



MAXIMUM RATINGS

(Ta=25°C)

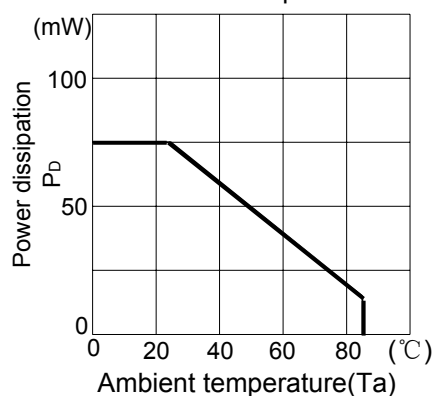
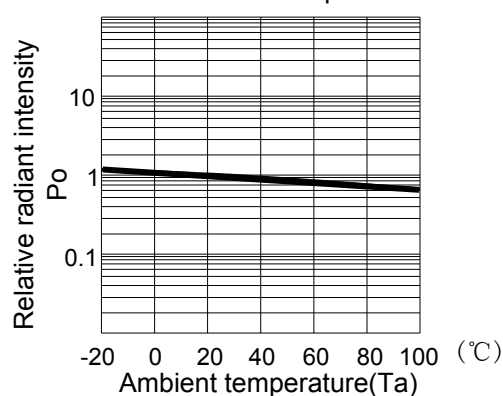
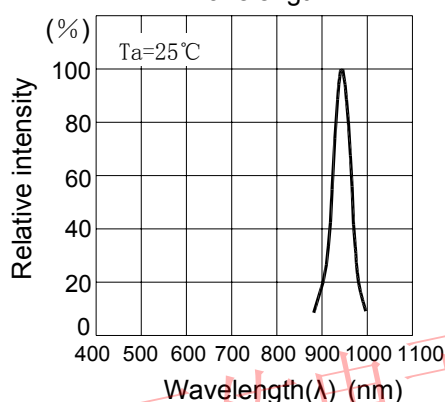
Item	Symbol	Ratings	Unit
Power dissipation	PD	170	mW
Forward current	IF	100	mA
Reverse voltage	VR	5	V
Operating temp.	Topr.	-25~+85	℃
Storage temp.	Tstg.	-30~+100	℃
Soldering temp. *	Tsol.	260	℃

* Lead Soldering Temperature (3mm from case for 5sec).

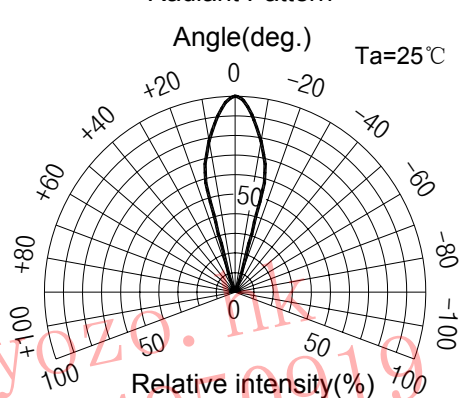
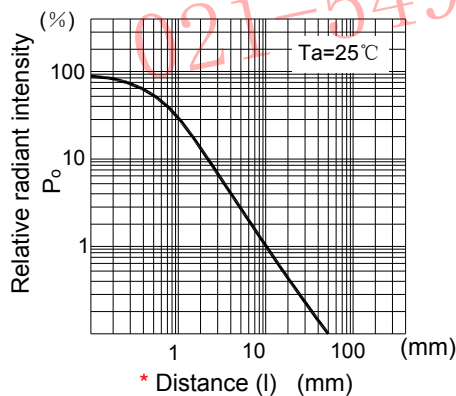
ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

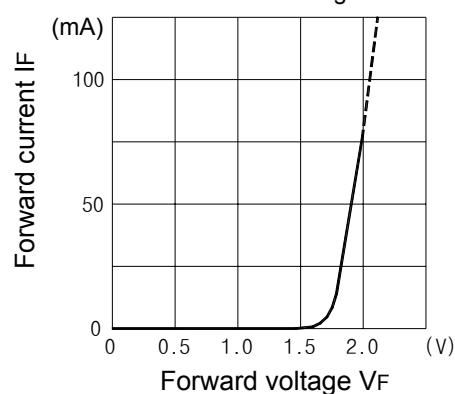
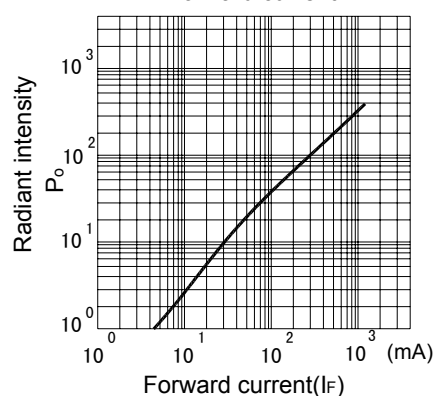
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V _F	I _F =50mA	-	1.4	1.7	V
Reverse current	I _R	V _R =5V	-	-	10	μA
Radiant intensity	I _E	I _F =50mA	30	50	-	mW/ster
Peak emission wavelength	λ _p	I _F =20mA	-	940	-	nm
Spectral bandwidth 50%	Δλ	I _F =20mA	-	45	-	nm
Half angle	Δθ	I _F =20mA	-	±16.5	-	deg.

Power dissipation Vs.
Ambient temperature元佐电子www.yozo.hk
021-54953990/54950919Relative radiant intensity
Vs. Ambient temperatureRelative intensity Vs.
Wavelength元佐电子www.yozo.hk
021-54953990/54950919

Radiant Pattern

Relative radiant intensity Vs.
Distance

* Distance (l) (mm)

Forward current Vs.
Forward voltageRadiant intensity Vs.
Forward current

*

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